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(54) **DISPLAY DEVICE AND MANUFACTURING METHOD OF DISPLAY DEVICE**

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(57) **ABSTRACT**

A display device with high resolution is provided. The display device includes a light-emitting element including a first electrode, an organic compound layer, and a second electrode; a first transistor electrically connected to the first electrode; a second transistor electrically connected to a gate of the first transistor; and an insulator provided to cover an end portion of the first electrode. The first transistor contains silicon in a channel formation region. The second transistor includes an oxide semiconductor in a channel formation region. An end portion of the organic compound layer is positioned in the opening portion of the insulator.